

# FQD6N60C

## 600V N-Channel MOSFET

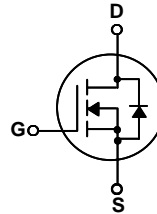
### Features

- 4 A, 600 V,  $R_{DS(on)} = 2.0 \Omega @ V_{GS} = 10 \text{ V}$
- Low gate charge ( typical 16 nC )
- Low Crss ( typical 7 pF)
- Fast switching
- 100 % avalanche tested
- Improved dv/dt capability

### Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.



### Absolute Maximum Ratings

Symbol	Parameter	FQD6N60C	Units
$V_{DSS}$	Drain-Source Voltage	600	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	4
		- Continuous ( $T_C = 100^\circ\text{C}$ )	2.4
$I_{DM}$	Drain Current - Pulsed (Note 1)	16	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	300	mJ
$I_{AR}$	Avalanche Current (Note 1)	4.0	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	8.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ )		80
		- Derate above $25^\circ\text{C}$	0.78
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.56	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	$^\circ\text{C/W}$

\*When mounted on the minimum pad size recommended (PCB Mount)

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQD6N60C	FQD6N60CTM	DPAK	380mm	16mm	2500
FQD6N60C	FQD6N60CTF	DPAK	380mm	16mm	2000

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

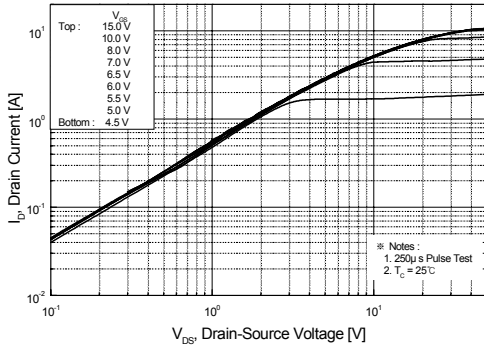
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	600	--	--	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	--	0.6	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	--	--	1	μA
		V <sub>DS</sub> = 480 V, T <sub>C</sub> = 125°C	--	--	10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	--	4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.0 A	--	1.7	2.0	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 2.0 A (Note 4)	--	4.8	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	--	620	810	pF
C <sub>oss</sub>	Output Capacitance		--	65	85	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	7	10	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 300 V, I <sub>D</sub> = 5.5 A, R <sub>G</sub> = 25 Ω (Note 4, 5)	--	15	40	ns
t <sub>r</sub>	Turn-On Rise Time		--	45	100	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	45	100	ns
t <sub>f</sub>	Turn-Off Fall Time		--	45	100	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 480 V, I <sub>D</sub> = 5.5 A, V <sub>GS</sub> = 10 V (Note 4, 5)	--	16	20	nC
Q <sub>gs</sub>	Gate-Source Charge		--	3.5	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	6.5	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	4.0	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	16	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 4.0 A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 5.5 A, di <sub>F</sub> / dt = 100 A/μs (Note 4)	--	310	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	2.1	--	μC

### Notes:

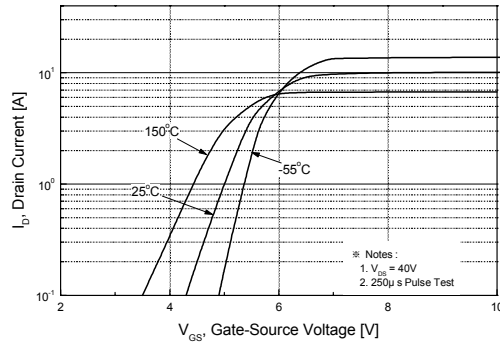
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 34.3 mH, I<sub>AS</sub> = 4.0 A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 4.0 A, di/dt ≤ 200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

## Typical Performance Characteristics

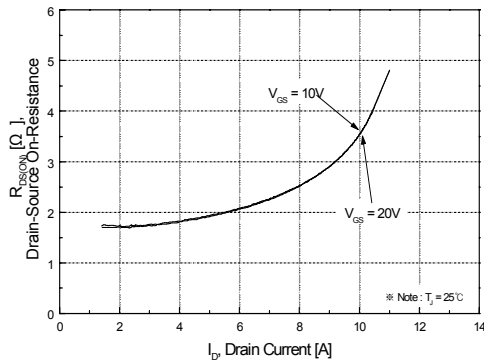
**Figure 1. On-Region Characteristics**



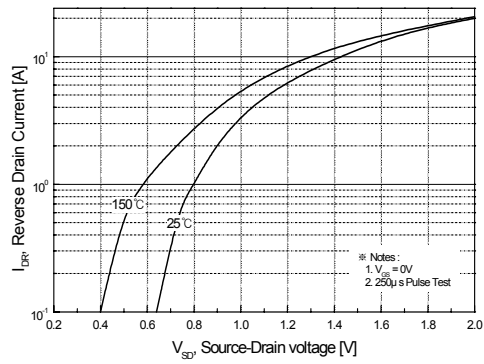
**Figure 2. Transfer Characteristics**



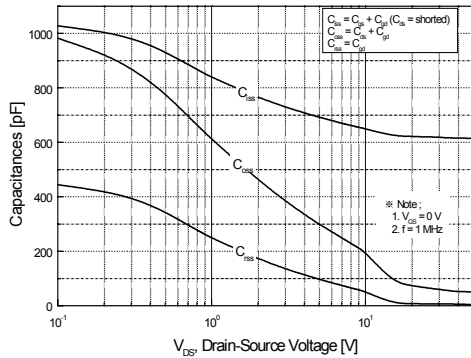
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



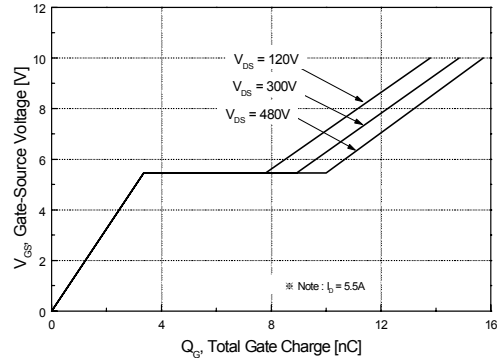
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

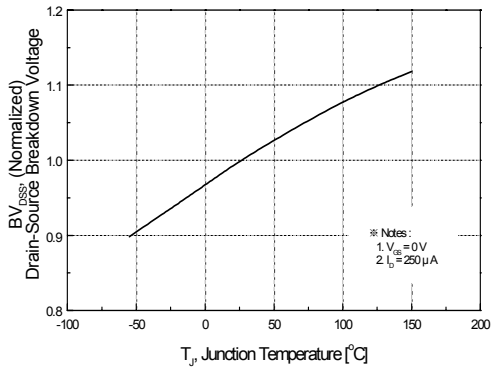


**Figure 6. Gate Charge Characteristics**

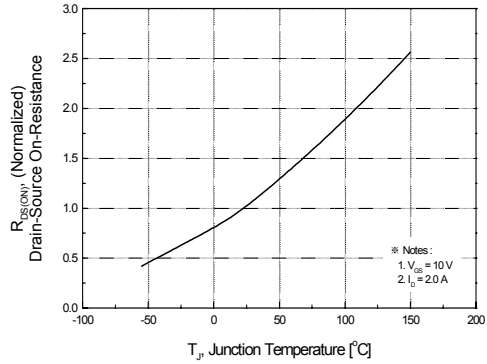


**Typical Performance Characteristics** (Continued)

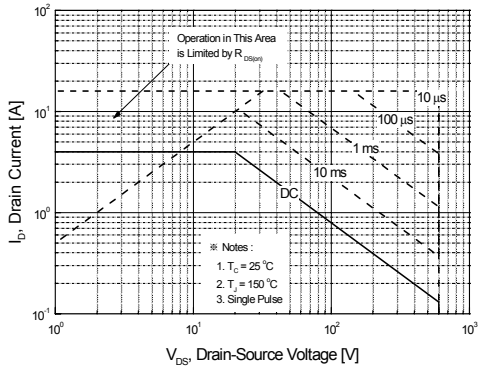
**Figure 7. Breakdown Voltage Variation vs. Temperature**



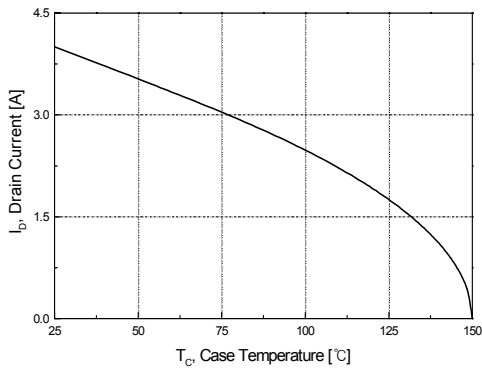
**Figure 8. On-Resistance Variation vs. Temperature**



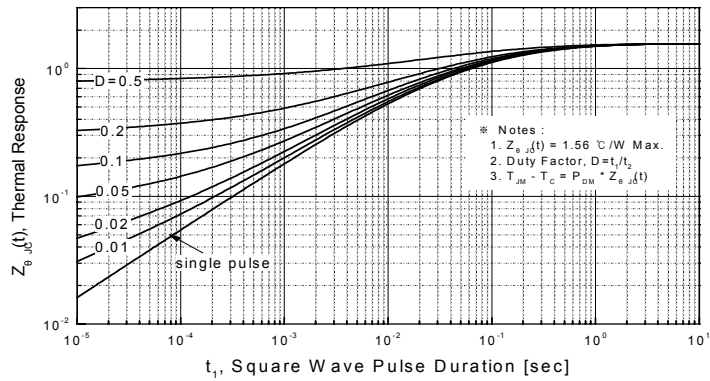
**Figure 9. Maximum Safe Operating Area**



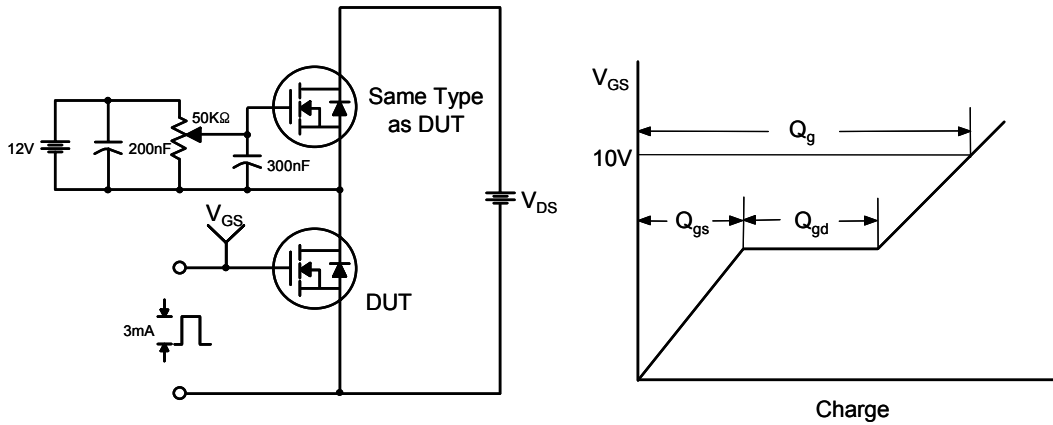
**Figure 10. Maximum Drain Current vs. Case Temperature**



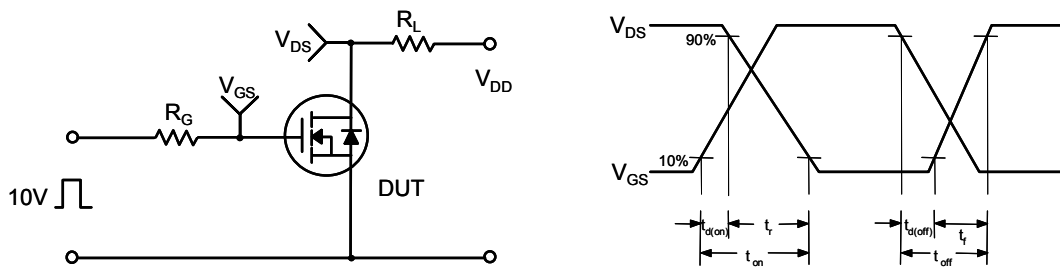
**Figure 11. Transient Thermal Response Curve**



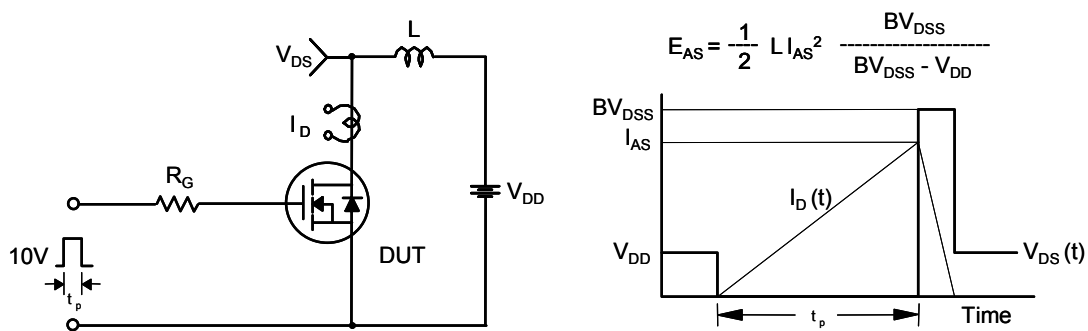
**Gate Charge Test Circuit & Waveform**



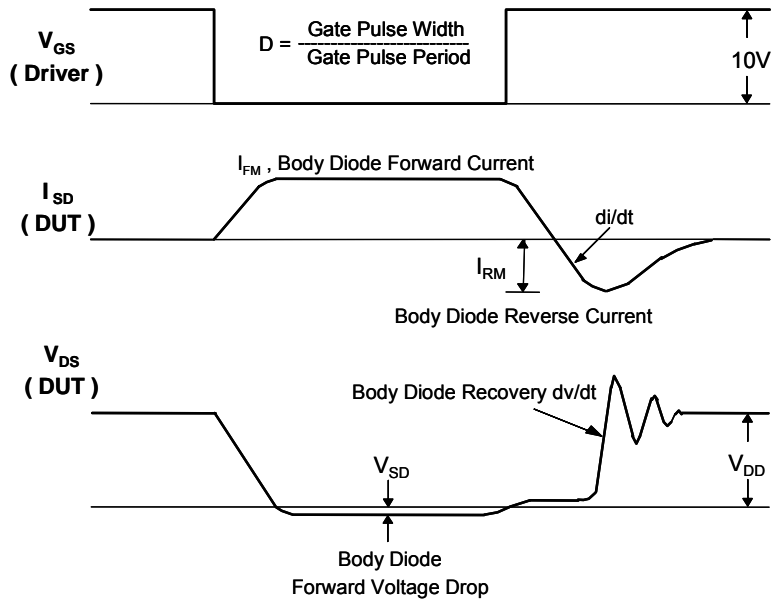
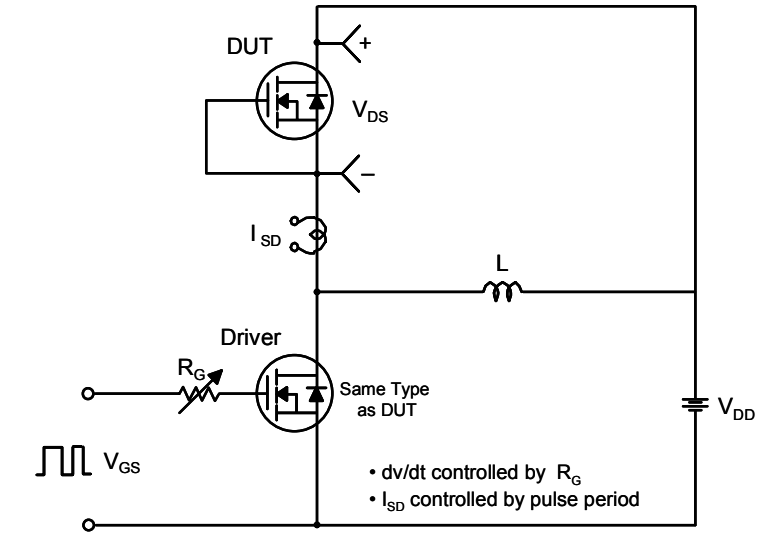
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

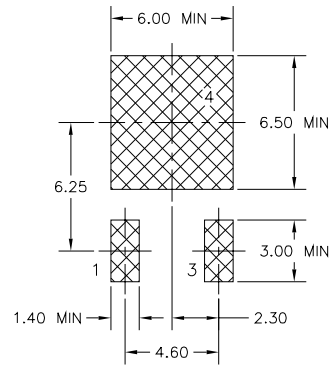
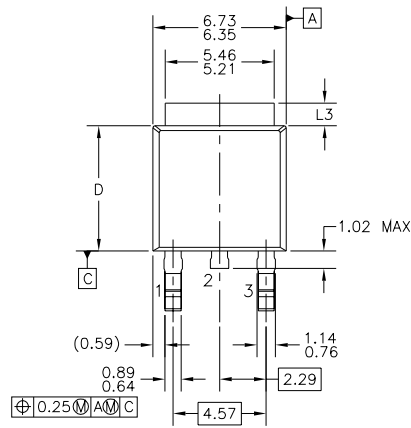


Peak Diode Recovery dv/dt Test Circuit & Waveforms

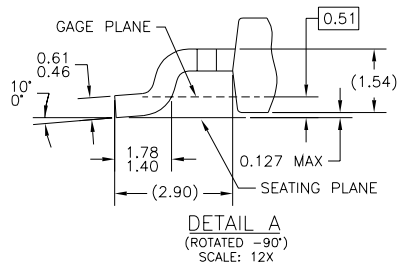
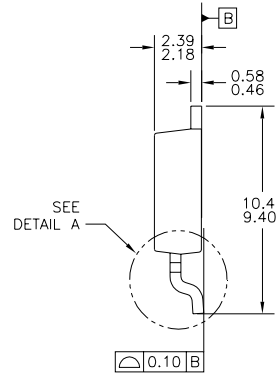
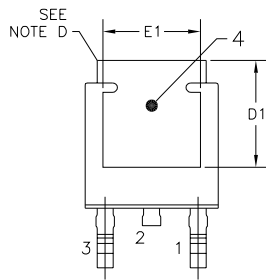


**Mechanical Dimensions**

**D-PAK**



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA & AB, DATED NOV. 1999.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) DIMENSIONS L3,D,E1&D1 TABLE:

	OPTION AA	OPTION AB
L3	0.89-1.27	1.52-2.03
D	5.97-6.22	5.33-5.59
E1	4.52 MIN	3.81 MIN
D1	5.21 MIN	4.57 MIN

- F) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

Dimensions in Millimeters

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CROSSVOLT™	GlobalOptoisolator™	MicroFET™	PowerTrench®	SuperSOT™_6
DOME™	GTO™	MicroPak™	QFET®	SuperSOT™_8
EcoSPARK™	HiSeC™	MICROWIRE™	QS™	SyncFET™
E <sup>2</sup> C MOS™	I <sup>2</sup> C™	MSX™	QT Optoelectronics™	TinyLogic®
EnSigna™	i-Lo™	MSXPro™	Quiet Series™	TINYOPTO™
FACT™	ImpliedDisconnect™	OCX™	RapidConfigure™	TruTranslation™
FACT Quiet Series™		OCXPro™	RapidConnect™	UHC™
Across the board. Around the world.™		OPTOLOGIC®	µSerDes™	UltraFET®
The Power Franchise®		OPTOPLANAR™	SILENT SWITCHER®	UniFET™
Programmable Active Droop™		PACMAN™	SMART START™	VCX™

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Datasheet Identification	Product Status	Definition
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Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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